NTGS3447P

Power MOSFET

−12 V, −5.3 A, Single P−Channel, TSOP−6

Features

- Low $R_{DS(on)}$ in TSOP−6 Package
- 1.8 V Gate Rating
- This is a Pb−Free Device

Applications

- Battery Switch and Load Management Applications in Portable Equipment
- High Side Load Switch
- PA Switch

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−12	V
Gate−to−Source Voltage			V_{GS}	±8	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−4.7	A
		T_A = 85°C		−3.4	
	t ≤ 5 s	T_A = 25°C		−5.3	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.25	W
	t ≤ 5 s			1.6	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	−3.4	A
		T_A = 85°C		−2.5	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.7	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−19	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

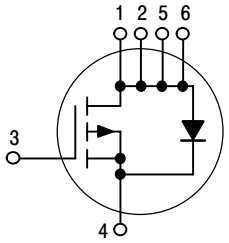
1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
2. Surface−mounted on FR4 board using the minimum recommended pad size.

ON Semiconductor®

http://onsemi.com

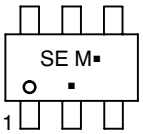
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
−12 V	40 mΩ @ −4.5 V	−4.7 A
	53 mΩ @ −2.5 V	−4.1 A
	72 mΩ @ −1.8 V	−2.0 A

P−Channel



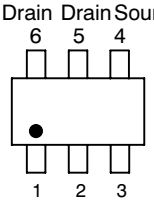
MARKING DIAGRAM

TSOP−6
CASE 318G
STYLE 1



SE = Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTGS3447PT1G	TSOP−6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	100	°C/W
Junction−to−Ambient − t ≤ 5 s (Note 3)	$R_{\theta JA}$	78	
Junction−to−Ambient − Minimum Pad (Note 4)	$R_{\theta JA}$	188	

3. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
4. Surface−mounted on FR4 board using the minimum recommended pad size (Cu area = 0.0775 in sq).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−12			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −12 V	T_J = 25°C			−1.0	μA
			T_J = 85°C			−5.0	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V				±0.1	μA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.45		−1.0	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −4.7 A			30	40	mΩ
		V_{GS} = −2.5 V, I_D = −4.1 A			40	53	
		V_{GS} = −1.8 V, I_D = −2.0 A			53	72	
Forward Transconductance	g_{FS}	V_{DS} = −5 V, I_D = −4.7 A			12		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −6 V			1053		pF
Output Capacitance	C_{OSS}				254		
Reverse Transfer Capacitance	C_{RSS}				129		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −6 V; I_D = −4.7 A			10.4	15	nC
Threshold Gate Charge	$Q_{G(TH)}$				1.0		
Gate−to−Source Charge	Q_{GS}				1.7		
Gate−to−Drain Charge	Q_{GD}				0.4		
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 6)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DS} = −6 V, I_D = −1.0 A, R_G = 6.0 Ω			7	11	ns
Rise Time	t_r				14	22	
Turn−Off Delay Time	$t_{d(OFF)}$				78	117	
Fall Time	t_f				47	71	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.7 A	T_J = 25°C		−0.7	−1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_{SD}/d_t = 100 A/μs, I_S = −1.7 A			33	66	ns

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
6. Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

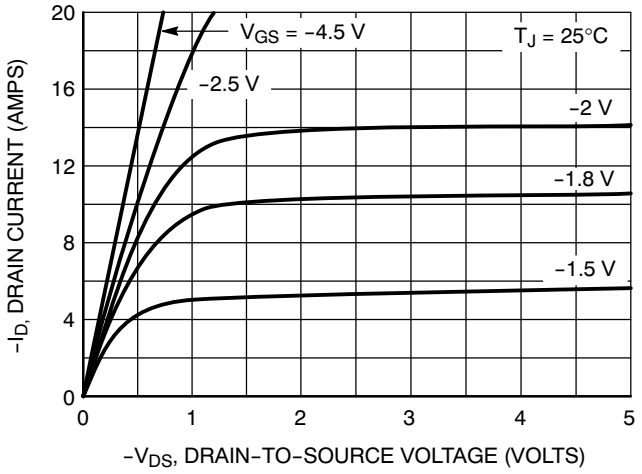


Figure 1. On−Region Characteristics

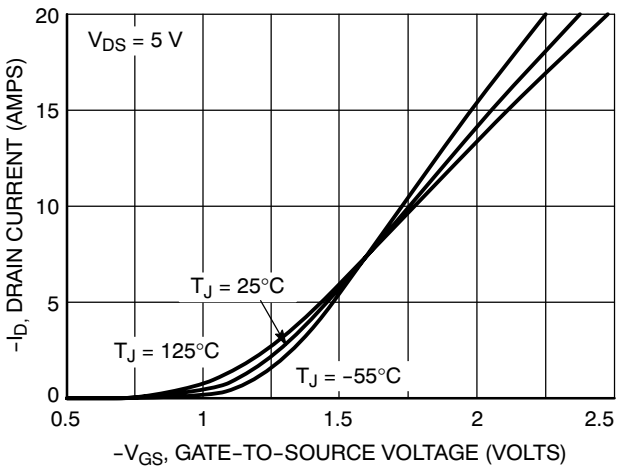


Figure 2. Transfer Characteristics

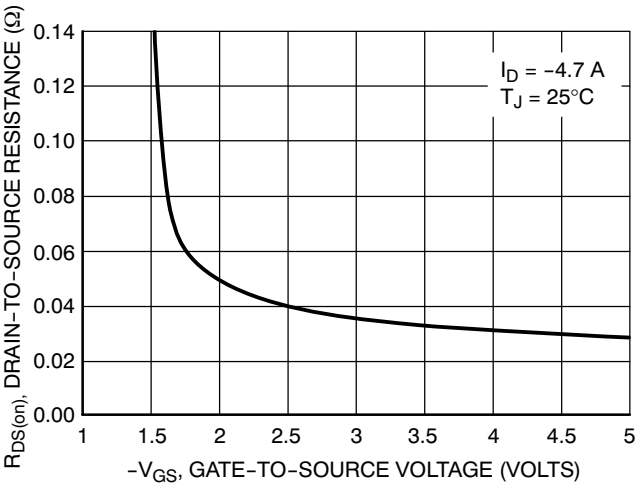


Figure 3. On−Resistance vs. Gate−to−Source Voltage

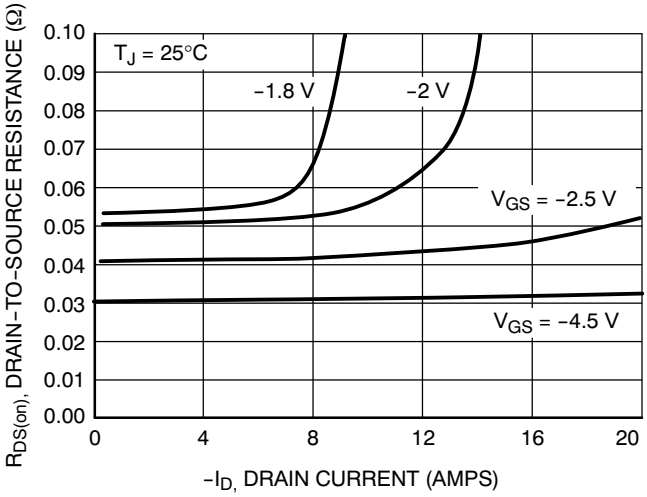


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

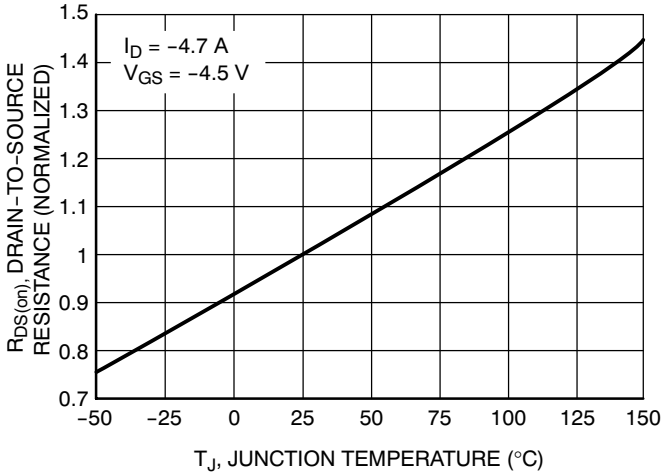


Figure 5. On−Resistance Variation with Temperature

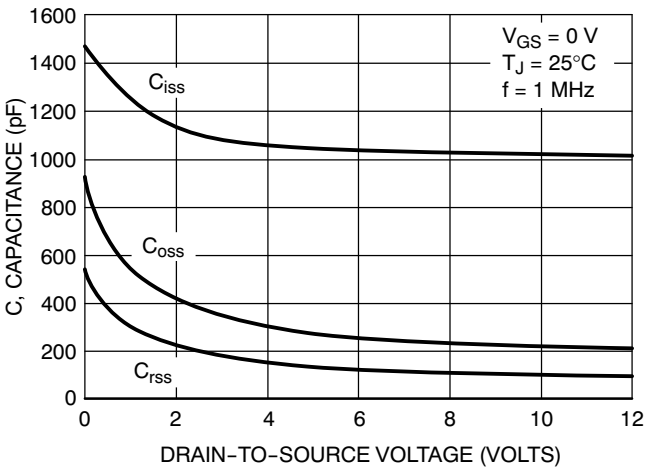


Figure 6. Capacitance Variation

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

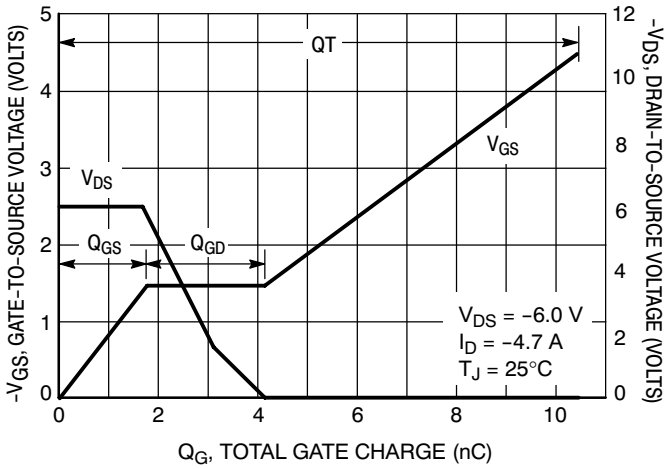


Figure 7. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

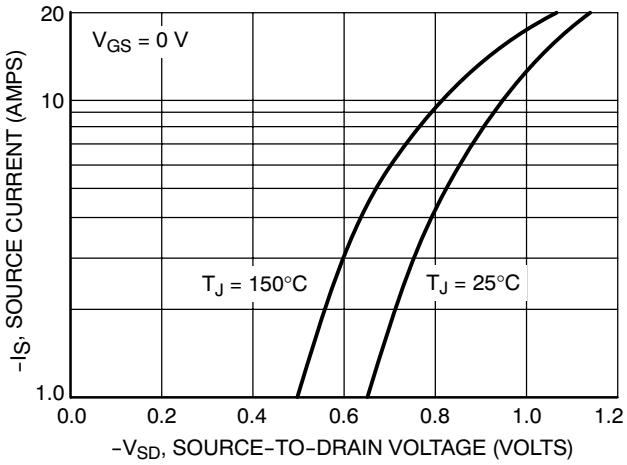


Figure 8. Diode Forward Voltage vs. Current

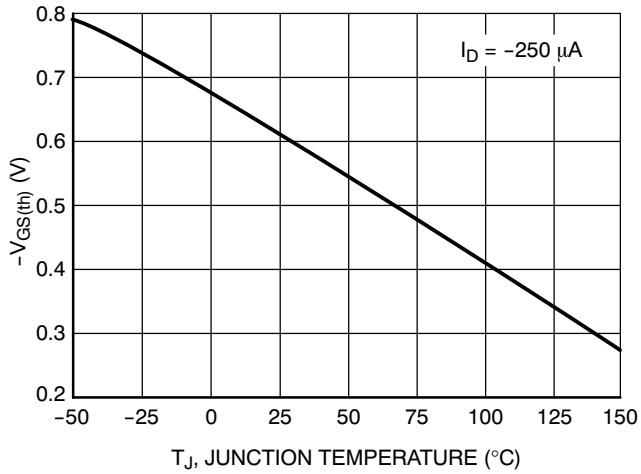


Figure 9. Threshold Voltage

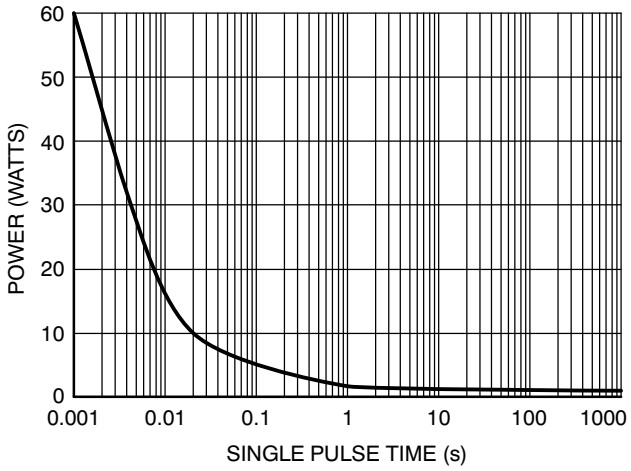


Figure 10. Single Pulse Maximum Power Dissipation

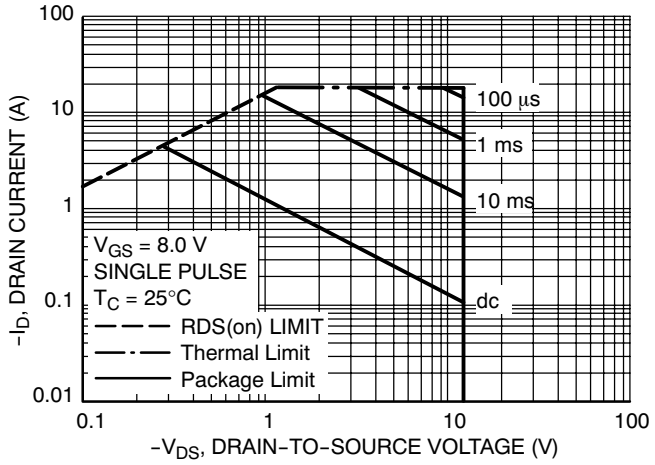


Figure 11. Maximum Rated Forward Biased Safe Operating Area

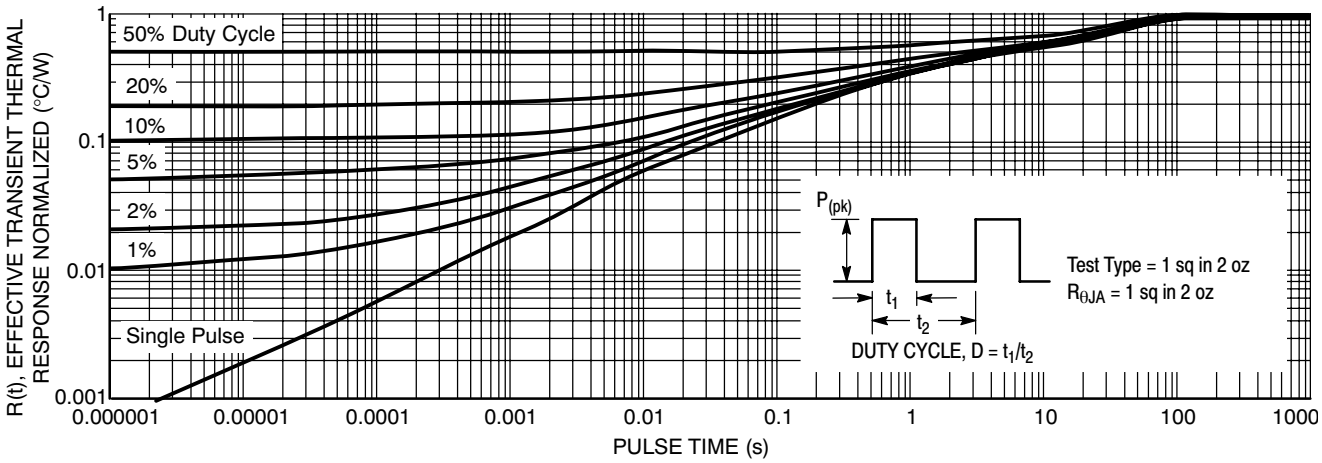
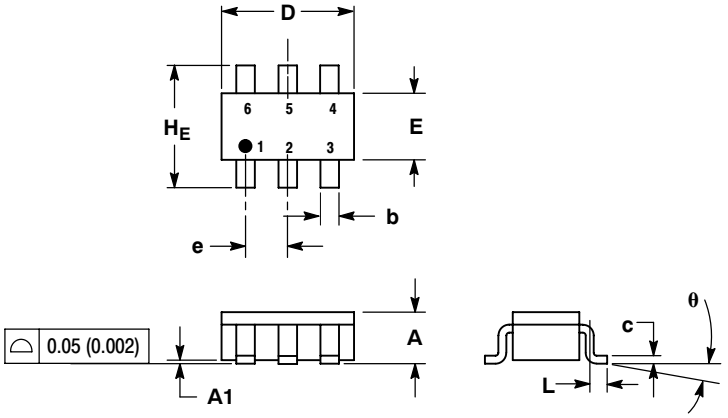


Figure 12. FET Thermal Response

PACKAGE DIMENSIONS

TSOP−6
CASE 318G−02
ISSUE S

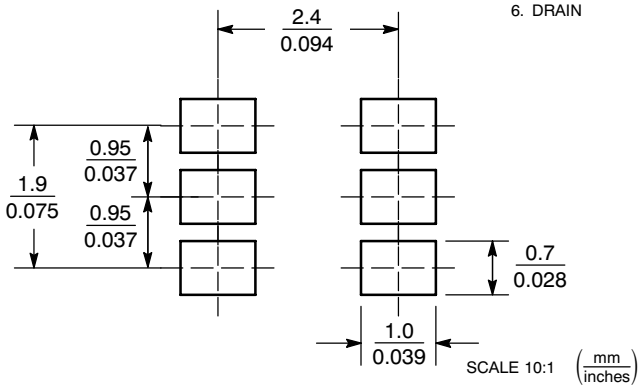


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	–	10°	0°	–	10°

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative